FAIRCHILD

SEMICONDUCTOR

MM74HCT138 3-to-8 Line Decoder

General Description

The MM74HCT138 decoder utilizes advanced silicon-gate CMOS technology, and are well suited to memory address decoding or data routing applications. Both circuits feature high noise immunity and low power consumption usually associated with CMOS circuitry, yet have speeds comparable to low power Schottky TTL logic.

The MM74HCT138 have 3 binary select inputs (A, B, and C). If the device is enabled these inputs determine which one of the eight normally HIGH outputs will go LOW. Two active LOW and one active HIGH enables (G1, G2A and G2B) are provided to ease the cascading decoders.

The decoders' output can drive 10 low power Schottky TTL equivalent loads and are functionally and pin equivalent to

the 74LS138. All inputs are protected from damage due to static discharge by diodes to V_{CC} and ground.

February 1984

Revised February 1999

MM74HCT devices are intended to interface between TTL and NMOS components and standard CMOS devices. These parts are also plug-in replacements for LS-TTL devices and can be used to reduce power consumption in existing designs.

Features

- TTL input compatible
- Typical propagation delay: 20 ns
- Low quiescent current: 80 µA maximum (74HCT Series)
- Low input current: 1 µA maximum
- Fanout of 10 LS-TTL loads

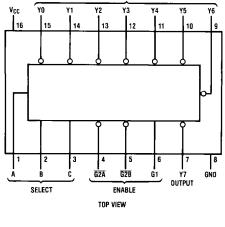
Ordering Code:

Package Number	Package Description
M16A	16-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
M16D	16-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
MTC16	16-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
N16E	16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide
	M16A M16D MTC16

Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

Connection Diagram





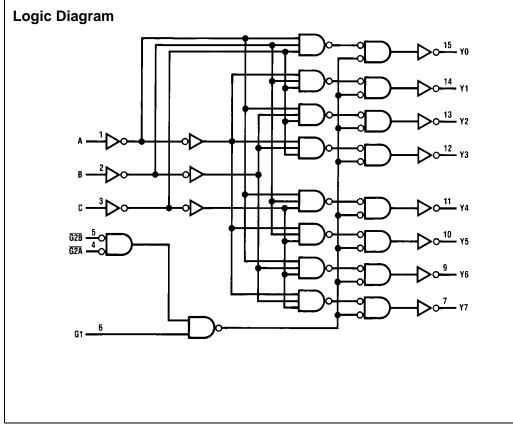


Truth Table

Inputs							Out	puts				
Er	nable	5	Selec	t								
G1	G2 (Note 1)	С	в	Α	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
Х	Н	Х	Х	Х	н	Н	Н	Н	Н	Н	Н	Н
L	х	Х	Х	Х	н	н	н	н	н	н	н	н
н	L	L	L	L	L	н	н	н	н	н	н	н
н	L	L	L	н	н	L	н	н	н	н	н	н
н	L	L	н	L	н	н	L	н	н	н	н	н
н	L	L	н	н	н	н	н	L	н	н	н	н
н	L	н	L	L	н	н	н	н	L	н	н	н
н	L	н	L	н	н	н	н	н	н	L	н	н
н	L	н	н	L	н	н	н	н	н	н	L	н
н	L	н	н	н	н	н	н	н	н	н	н	L

H = HIGH Level L = LOW Level X = Don't Care

Note 1: $\overline{G2} = \overline{G2A} + \overline{G2B}$



Absolute Maximum Ratings(Note 2)

Recommended Operating Conditions

	-
(Note 3)	
Supply Voltage (V _{CC})	-0.5 to +7.0V
DC Input Voltage (V _{IN})	-1.5 to V _{CC} $+1.5$ V
DC Output Voltage (V _{OUT})	–0.5 to V_{CC} +0.5V
Clamp Diode Current (I _{IK} , I _{OK})	±20 mA
DC Output Current, per pin (I _{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I _{CC})	±50 mA
Storage Temperature Range (T _{STG})	-65°C to +150°C
Power Dissipation (P _D)	
(Note 4)	600 mW
S.O. Package only	500 mW
Lead Temperature (TL)	
(Soldering 10 seconds)	260°C

	Min	Max	Units
Supply Voltage (V _{CC})	4.5	5.5	V
DC Input or Output Voltage			
(V _{IN} , V _{OUT})	0	V_{CC}	V
Operating Temperature Range (T _A)	-40	+85	°C
Input Rise or Fall Times			
(t _r , t _f)		500	ns
Note 2: Absolute Maximum Ratings are those age to the device may occur.	values b	eyond whi	ch dam-

Note 3: Unless otherwise specified all voltages are referenced to ground. Note 4: Power Dissipation temperature derating — plastic "N" package: – 12 mW/°C from 65°C to 85°C.

DC Electrical Characteristics

Symbol	Parameter	Conditions	T _A =	= 25°C	$T_A = -40 \text{ to } 85^\circ C$	$T_A = -55$ to $125^{\circ}C$	Units
	rarameter		Тур		Guaranteed L	imits	Unita
VIH	Minimum HIGH Level			2.0	2.0	2.0	V
	Input Voltage						
VIL	Maximum LOW Level			0.8	0.8	0.8	V
	Input Voltage						
V _{OH}	Minimum HIGH Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$					
	Output Voltage	$ I_{OUT} = 20 \ \mu A$	V _{CC}	V _{CC} -0.1	V _{CC} - 0.1	V _{CC} - 0.1	V
		$ I_{OUT} = 4.0 \text{ mA}, V_{CC} = 4.5 \text{V}$	4.2	3.98	3.84	3.7	V
		$ I_{OUT} = 4.8 \text{ mA}, V_{CC} = 5.5 \text{V}$	5.2	4.98	4.84	4.7	V
V _{OL}	Maximum LOW Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$					
	Voltage	$ I_{OUT} = 20 \ \mu A$	0	0.1	0.1	0.1	V
		$ I_{OUT} = 4.0 \text{ mA}, V_{CC} = 4.5 \text{V}$	0.2	0.26	0.33	0.4	V
		$ I_{OUT} = 4.8 \text{ mA}, V_{CC} = 5.5 \text{V}$	0.2	0.26	0.33	0.4	V
I _{IN}	Maximum Input	$V_{IN} = V_{CC}$ or GND,		±0.1	±1.0	±1.0	μΑ
	Current	V _{IH} or V _{IL}					
I _{CC}	Maximum Quiescent	$V_{IN} = V_{CC}$ or GND		8.0	80	160	μΑ
	Supply Current	$I_{OUT} = 0 \ \mu A$					
		V _{IN} = 2.4V or 0.5V (Note 5)	1	0.3	0.4	0.5	mA

Note 5: This is measured per input pin. All other inputs are held at V_{CC} or ground.

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AC Electrical Characteristics

T_{A} = 25°C, V_{CC} = 5.0V, t_{f} = t_{\text{f}} = 6 ns, C_{L} = 15 pF (unless otherwise specified)

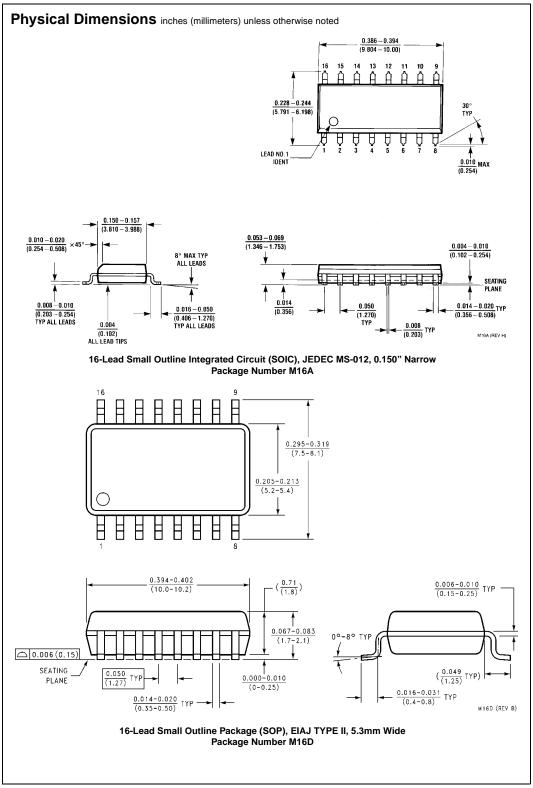
Symbol	Parameter	Conditions	Тур	Guaranteed Limit	Units
t _{PHL}	Maximum Propagation Delay, A, B, or C to Output		20	35	ns
t _{PLH}	Maximum Propagation Delay, A, B, or C to Output		13	25	ns
t _{PHL}	Maximum Propagation Delay, G1 to Y Output		14	25	ns
t _{PLH}	Maximum Propagation Delay, G1 to Y Output		13	25	ns
t _{PHL}	Maximum Propagation Delay, G2A or G2B to Y Output		17	30	ns
t _{PLH}	Maximum Propagation Delay, G2A or G2B to Y Output		13	25	ns

AC Electrical Characteristics

 $V_{CC} = 5V \pm 10\%$, $C_L = 50$ pF, $t_r = t_f = 6$ ns (unless otherwise specified)

Symbol	Parameter	Conditions	T _A =	25°C	$T_A = -40$ to $85^{\circ}C$	$T_A = -55 \text{ to } 125^\circ C$	Units
		Contaitions	Тур		Guaranteed L	imits	onno
t _{PHL}	Maximum Propagation Delay		24	40	50	60	ns
	A, B, or C to Output						
t _{PLH}	Maximum Propagation Delay		18	30	38	45	ns
	A, B, or C to Output						
t _{PHL}	Maximum Propagation Delay		17	30	38	45	ns
	G1 to Y Output						
t _{PLH}	Maximum Propagation Delay		20	30	38	45	ns
	G1 to Y Output						
t _{PHL}	Maximum Propagation Delay		23	35	43	52	ns
	G2A or G2B to Y Output						
t _{PLH}	Maximum Propagation Delay		18	30	38	45	ns
	$\overline{\text{G2A}}$ or $\overline{\text{G2B}}$ to Y Output						
t _{THL} , t _{TLH}	Maximum Output			15	19	22	ns
	Rise and Fall Time						
CIN	Input Capacitance			5	10	10	pF
C _{PD}	Power Dissipation		55				pF
	Capacitance	(Note 6)					

Note 6: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.



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